

Darlington Transistors

PNP Silicon

MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G,

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CES}	-30	Vdc
Collector - Base Voltage	V _{CBO}	-30	Vdc
Emitter – Base Voltage	V _{EBO}	-10	Vdc
Collector Current - Continuous	Ic	-500	mAdc

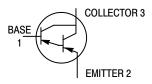
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.





MARKING DIAGRAM



2x = Device Code

x = U for MMBTA63LT1G x = V for MMBTA64LT1G SMMBTA64LT1G

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may
vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTA63LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA64LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA64LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA63LT1G, MMBTA64LT1G, SMMBTA64LT1G,

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I _C = -100 µAdc)	V _(BR) CEO	-30	-	Vdc
Collector Cutoff Current (V _{CB} = -30 Vdc)	І _{СВО}	-	-100	nAdc
Emitter Cutoff Current (V _{EB} = -10 Vdc)	I _{EBO}	-	-100	nAdc
ON CHARACTERISTICS				
DC Current Gain (Note 3) $ \begin{aligned} &(I_C=-10 \text{ mAdc, } V_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA63} \end{aligned} \\ &(I_C=-10 \text{ mAdc, } V_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA64, SMMBTA64} \end{aligned} \\ &(I_C=-100 \text{ mAdc, } V_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA63} \end{aligned} \\ &(I_C=-100 \text{ mAdc, } V_{CE}=-5.0 \text{ Vdc}) \\ &\text{MMBTA64, SMMBTA64} \end{aligned}$	h _{FE}	5,000 10,000 10,000 20,000	- - -	_
Collector – Emitter Saturation Voltage (I _C = -100 mAdc, I _B = -0.1 mAdc)	V _{CE(sat)}	-	-1.5	Vdc
Base – Emitter On Voltage (I _C = –100 mAdc, V _{CE} = –5.0 Vdc)	V _{BE(on)}	-	-2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				•
Current – Gain – Bandwidth Product (I _C = -10 mAdc, V _{CE} = -5.0 Vdc, f = 100 MHz)	f⊤	125	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

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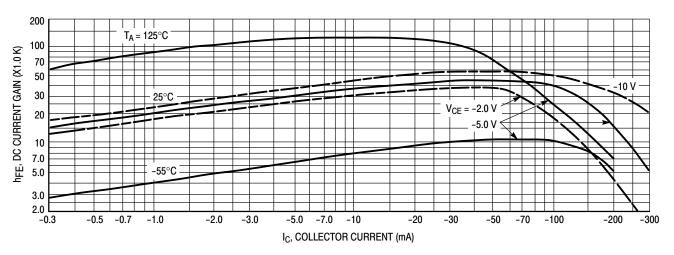


Figure 1. DC Current Gain

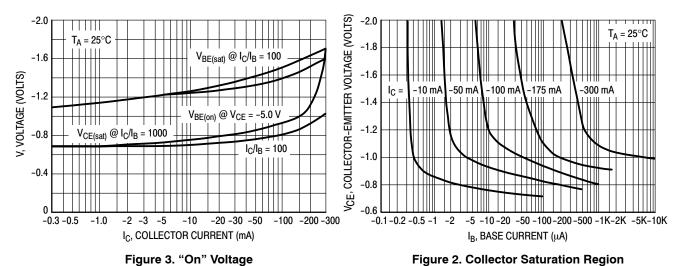


Figure 3. "On" Voltage

IhFEI, HIGH FREQUENCY CURRENT GAIN

4.0

3.0

2.0

1.0

0.4

V_{CE} = -5.0 V f = 100 MHz

_ T_A = 25°C

-2.0

-1.0

1 ms ₹ 10 ms IC, COLLECTOR CURRENT 0.1 100 ms 1 s 0.01 Thermal Limit Single Pulse Test @ $T_A = 25^{\circ}C$ 0.001 -500 -1K 0.01 1.0 100 V_{CE}, COLLECTOR-EMITTER VOLTAGE (V)

IC, COLLECTOR CURRENT (mA) Figure 4. High Frequency Current Gain

-50 -100 -200

-20

Figure 5. Safe Operating Area

MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40





SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024

MAX

1.11

0.10

0.50

0.20

3.04

1.40

2.04

0.55

0.69

2.64

10°





DETAIL "A" Scale 3:1







NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR			
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	2. CATHODE 2.	2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	2. ANODE 2.	3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT			STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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